TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS195

January 1998

CD74HC670, CD74HCT670

High-Speed CMOS Logic 4x4 Register File

Features

- Simultaneous and Independent Read and Write Operations
- Expandable to 512 Words of n-Bits
- Three-State Outputs
- Organized as 4 Words x 4 Bits Wide
- Buffered Inputs
- Typical Read Time = 16ns for CD74HC670 V_{CC} = 5V, C_L = 15pF, T_A = 25^oC
- Fanout (Over Temperature Range)
  - Standard Outputs . . . . . 10 LSTTL Loads
  - Bus Driver Outputs . . . . . 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55^oC to 125^oC
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
  - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}

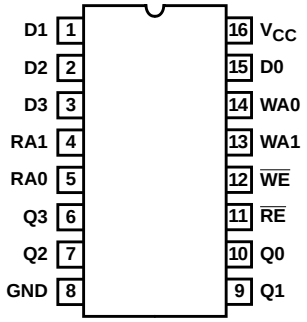
Description

The Harris CD74HC670 and CD74HCT670 are 16-bit register files organized as 4 words x 4 bits each. Read and write address and enable inputs allow simultaneous writing into one location while reading another. Four data inputs are provided to store the 4-bit word. The write address inputs (WA0 and WA1) determine the location of the stored word in the register. When write enable ($\overline{WE}$) is low the word is entered into the address location and it remains transparent to the data. The outputs will reflect the true form of the input data. When ($\overline{WE}$) is high data and address inputs are inhibited. Data acquisition from the four registers is made possible by the read address inputs (RA1 and RA0). The addressed word appears at the output when the read enable ($\overline{RE}$) is low. The output is in the high impedance state when the ($\overline{RE}$) is high. Outputs can be tied together to increase the word capacity to 512 x 4 bits.

Ordering Information

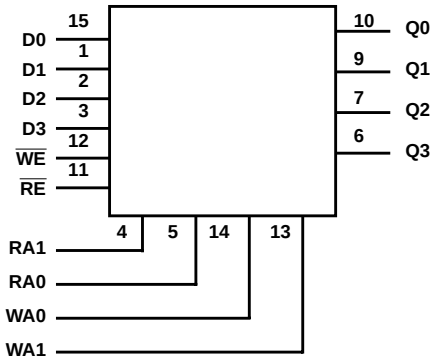
Pinout

CD74HC670, CD74HCT670
(PDIP, SOIC)
TOP VIEW



File Number **1660.1**

Functional Diagram



WRITE MODE SELECT TABLE

OPERATING MODE	INPUTS		INTERNAL LATCHES (NOTE 3)
	$\overline{WE}$	D_N	
Write Data	L	L	L
	L	H	H
Data Latched	H	X	No Change

NOTE:

3. The Write Address (WA0 and WA1) to the “internal latches” must be stable while $\overline{WE}$ is LOW for conventional operation.

READ MODE SELECT TABLE

OPERATING MODE	INPUTS		OUTPUT Q_N
	$\overline{RE}$	INTERNAL LATCHES (NOTE 4)	
Read	L	L	L
	L	H	H
Disabled	H	X	(Z)

NOTE:

4. The selection of the “internal latches” by Read Address (RA0 and RA1) are not constrained by $\overline{WE}$ or $\overline{RE}$ operation.
   H = High Voltage Level
   L = Low Voltage Level
   X= Don’t Care
   Z = High Impedance “Off” State

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Drain Current, per Output, I_O
For -0.5V < V_O < V_{CC} + 0.5V . . . . . ±35mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} . . . . . ±50mA

Operating Conditions

Temperature Range, T_A . . . . . -55^oC to 125^oC
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 5) θ_{JA} ($^oC/W$)
PDIP Package 90
SOIC Package 160
Maximum Junction Temperature . . . . . 150^oC
Maximum Storage Temperature Range . . . . . -65^oC to 150^oC
Maximum Lead Temperature (Soldering 10s) . . . . . 300^oC
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

5. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS V_I (V)	TEST CONDITIONS I_O (mA)	V_{CC} (V)	25°C MIN	25°C TYP	25°C MAX	-40°C TO 85°C MIN	-40°C TO 85°C MAX	-55°C TO 125°C MIN	-55°C TO 125°C MAX	UNITS
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA
Three- State Leakage Current		V_{IL} or V_{IH}	V_O = V_{CC} or GND	6	-	-	±0.5	-	±5.0	-	±10	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	0	5.5	-		±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Three- State Leakage Current		V_{IL} or V_{IH}	V_O = V_{CC} or GND	5.5	-	-	±0.5	-	±5.0	-	±10	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC}	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE: For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
$\overline{WE}$	0.3
WA0	0.2
WA1	0.4
$\overline{RE}$	1.5
DATA	0.15
RA0	0.4
RA1	0.7

NOTE: Unit load is ΔI_{CC} limit specific in DC Electrical Specifications Table, e.g., 360µA max. at 25°C.

Prerequisite for Switching Specifications

PARAMETER	SYMBOL	V_{CC} (V)	25°C			-40°C TO 85°C			-55°C TO 125°C			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
HC TYPES												
Setup Time Data to $\overline{WE}$ Write to $\overline{WE}$	t_{SU}, t_h	2	60	-	-	75	-	-	90	-	-	ns
		4.5	12	-	-	15	-	-	18	-	-	ns
		6	10	-	-	13	-	-	15	-	-	ns
Hold Time Data to $\overline{WE}$ Write to $\overline{WE}$	t_H, t_W	2	5	-	-	5	-	-	5	-	-	ns
		4.5	5	-	-	5	-	-	5	-	-	ns
		6	5	-	-	5	-	-	5	-	-	ns
Pulse Width $\overline{WE}$	t_W	2	80	-	-	100	-	-	120	-	-	ns
		4.5	16	-	-	20	-	-	24	-	-	ns
		6	14	-	-	17	-	-	20	-	-	ns
Latch Time $\overline{WE}$ to RA0, RA1	t_{LATCH}	2	100	-	-	125	-	-	150	-	-	ns
		4.5	20	-	-	25	-	-	30	-	-	ns
		6	17	-	-	21	-	-	26	-	-	ns
HCT TYPES												
Setup Time Data to $\overline{WE}$	t_{SU}, t_h	4.5	12	-	-	15	-	-	18	-	-	ns
Hold Time Data to $\overline{WE}$ Write to $\overline{WE}$	t_H, t_W	4.5	5	-	-	5	-	-	5	-	-	ns
Setup Time Write to $\overline{WE}$	t_{SU}	4.5	18	-	-	23	-	-	27	-	-	ns
Pulse Width $\overline{WE}$	t_W	4.5	20	-	-	25	-	-	30	-	-	ns
Latch Time $\overline{WE}$ to RA0, RA1	t_{LATCH}	4.5	25	-	-	31	-	-	38	-	-	ns

Switching Specifications C_L = 50pF, Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay Reading Any Word	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	195	-	245	-	295	ns
			4.5	-	-	39	-	49	-	59	ns
		C_L = 15pF	5	-	16	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	33	-	42	-	50	ns
Write Enable to Output	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	250	-	315	-	375	ns
			4.5	-	-	50	-	63	-	75	ns
		C_L = 15pF	5	-	21	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	43	-	54	-	64	ns

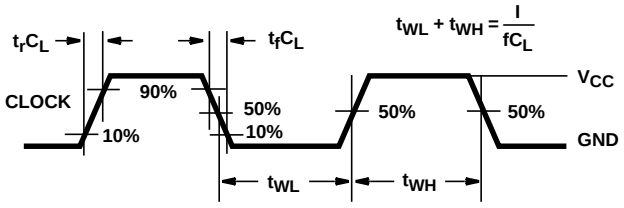
Switching Specifications C_L = 50pF, Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Data to Output	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	256	-	315	-	375	ns
			4.5	-	-	50	-	63	-	75	ns
		C_L = 15pF	5	-	21	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	43	-	54	-	64	ns
Output Disable Time	t_{PLZ}, t_{PHZ}	C_L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	26	-	33	-	38	ns
Output Enable Time	t_{PZL}, t_{PZH}	C_L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	26	-	33	-	38	ns
Output Transition Time	t_{THL}, t_{TLH}	C_L = 50pF	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	10	-	19	ns
Input Capacitance	C_I	C_L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 6, 7)	C_{PD}	C_L = 15pF	5	-	59	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay Reading Any Word	t_{PHL}, t_{PLH}	C_L = 50pF	4.5	-	-	40	-	50	-	53	ns
		C_L = 15pF	5	-	17	-	-	-	-	-	ns
Write Enable to Output	t_{PHL}, t_{PLH}	C_L = 50pF	4.5	-	-	50	-	63	-	75	ns
		C_L = 15pF	5	-	21	-	-	-	-	-	ns
Data to Output	t_{PHL}, t_{PLH}	C_L = 50pF	4.5	-	-	50	-	63	-	75	ns
		C_L = 15pF	5	-	21	-	-	-	-	-	ns
Output Disable Time	t_{PLZ}, t_{PHZ}	C_L = 50pF	4.5	-	-	35	-	44	-	53	ns
		C_L = 15pF	5	-	14	-	-	-	-	-	ns
Output Enable Time	t_{PZL}, t_{PZH}	C_L = 50pF	4.5	-	-	38	-	48	-	57	ns
		C_L = 15pF	5	-	16	-	-	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C_I	C_L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 6, 7)	C_{PD}	C_L = 15pF	5	-	66	-	-	-	-	-	pF

NOTES:

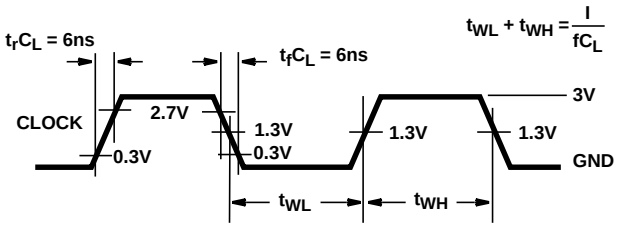
6. C_{PD} is used to determine the dynamic power consumption, per output.
7. $P_D = C_{PD} V_{CC}^2 f_i + \Sigma C_L V_{CC}^2 f_O$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 1. HC CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 2. HCT CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

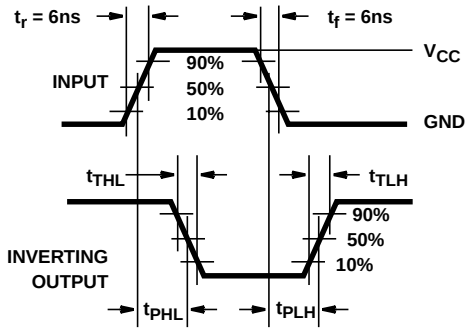


FIGURE 3. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

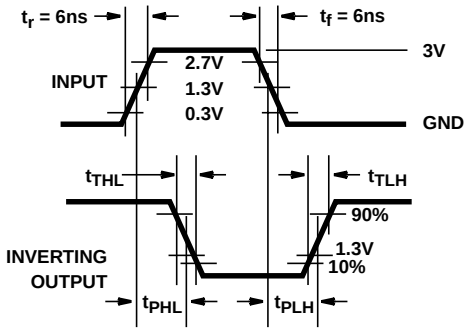


FIGURE 4. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

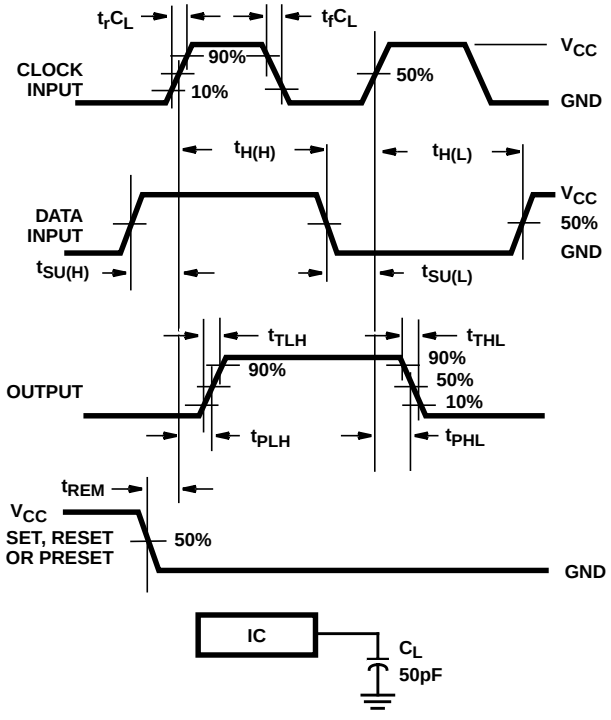


FIGURE 5. HC SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

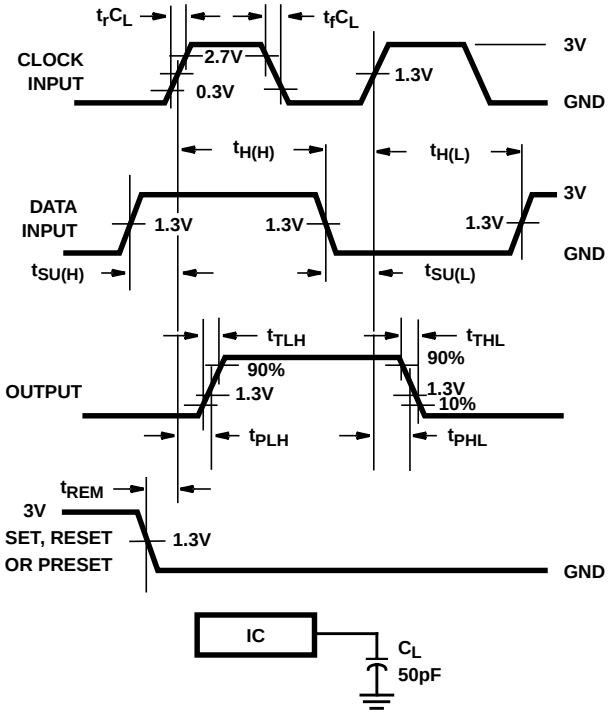


FIGURE 6. HCT SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

Test Circuits and Waveforms (Continued)

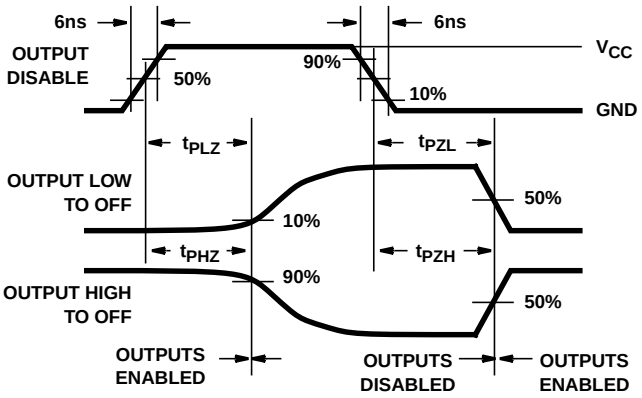


FIGURE 7. HC THREE-STATE PROPAGATION DELAY WAVEFORM

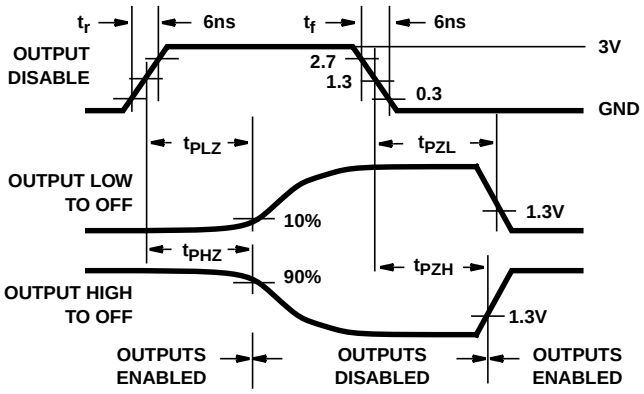
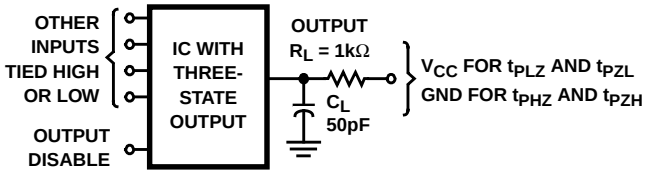


FIGURE 8. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output R_L = 1kΩ to V_{CC}, C_L = 50pF.

FIGURE 9. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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